

Modeling hysteretic effects in perovskite solar cells

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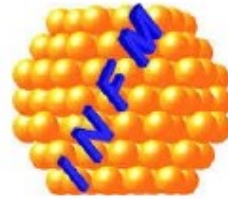
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Outline

- Perovskite solar cells

High power conversion efficiency (PCE>22%), Stability issues, Hysteretic effects

- Dynamic electrical model (DEM):

Equivalent circuit model, introducing a non-linear polarization component.

[1] G. A. Nemnes et al, “*Dynamic electrical behavior of halide perovskite based solar cells*”,
Solar Energy Materials and Solar Cells 159, 197 (2017)

- Normal and inverted hysteresis effects:

Bias pre-poling and bias scan rate effects (theory and experiment)

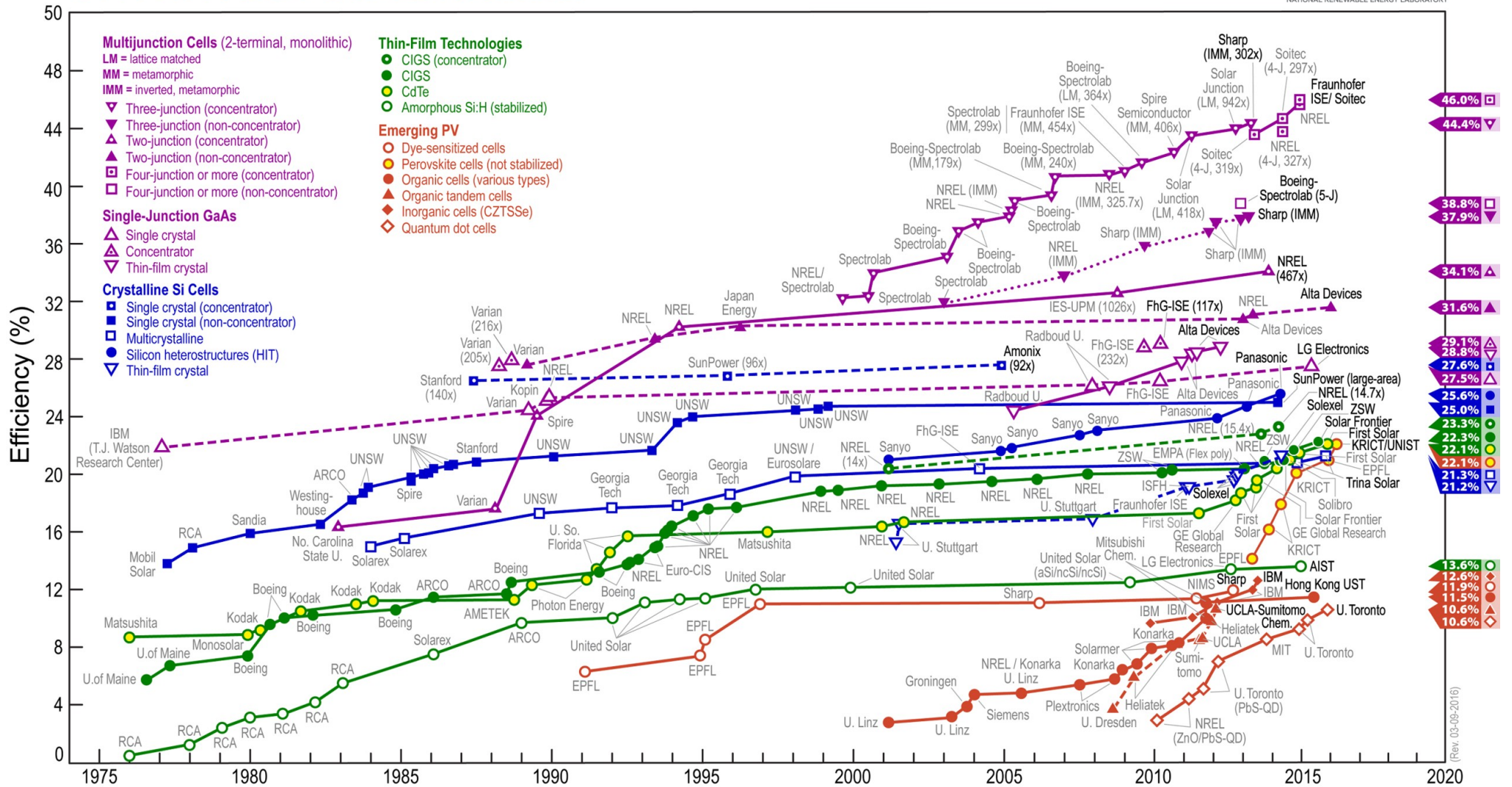
[2] G. A. Nemnes et al, “*Normal and inverted hysteresis in perovskite solar cells*”,
J. Phys. Chem. C 121, 11207 (2017)

- Measurement protocol:

The importance of correlated forward and reverse bias scans

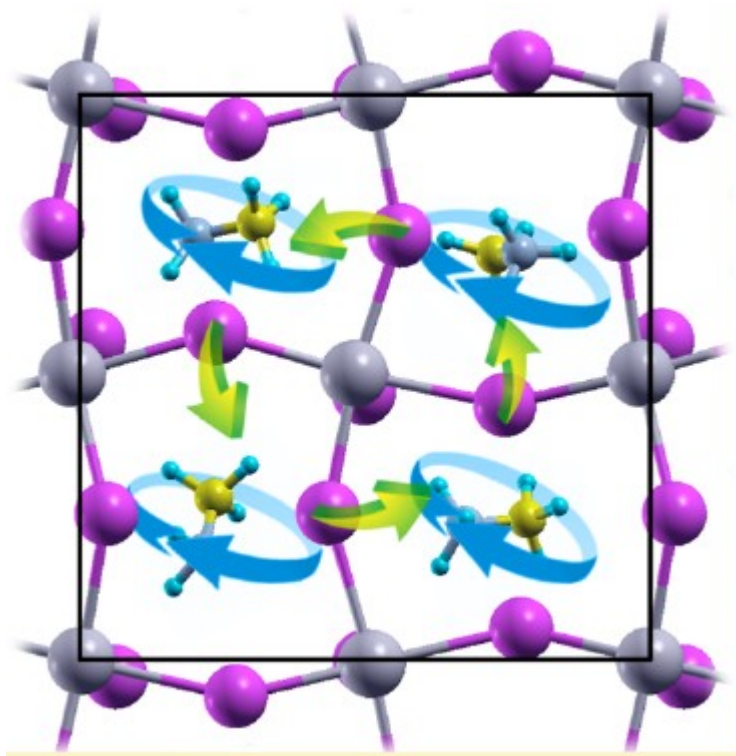
- Conclusions

Best Research-Cell Efficiencies



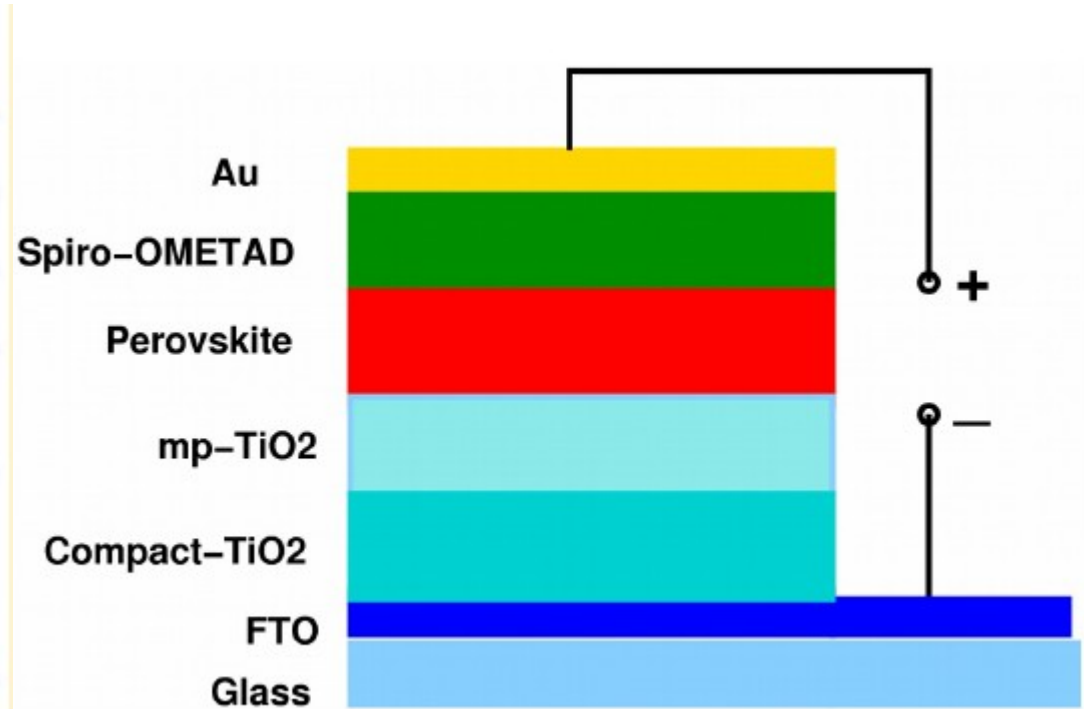
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Material properties and device structure



$\text{CH}_3\text{NH}_3\text{PbI}_3$ (MAPI)

High absorption coefficient, carrier mobility and diffusion length ($> 1 \mu\text{m}$)



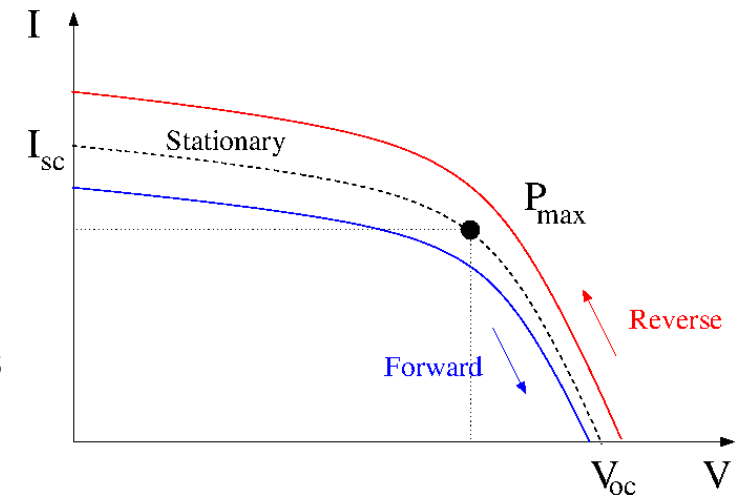
Dynamic J-V hysteresis

- Dynamic hysteresis:

- Forward and reverse bias scans yield different I-V characteristics (typically larger currents in reverse, explained by capacitive effects → *normal hysteresis*)
- Depends on the pre-conditioning of the solar cell and on the bias scan rate

- Possible reasons for the hysteretic effects:

- Giant dielectric constant
- Ferroelectricity of the perovskite layer
- Ion migration + accumulation of charges
- Trapping-detrapping of charges
- Unbalanced distributions of electrons and holes

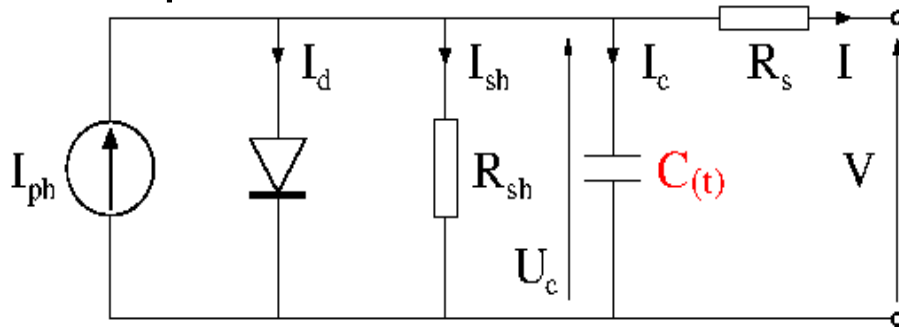


- Why investigate hysteretic effects ?

- A challenge for a *correct determination of the PCE.*
- But it provides *further insight about the solar cell operation.*
- Can be correlated *with solar cell degradation*

Dynamic electrical model (DEM)

Equivalent circuit:



$$I_{ph} = I_d + I_{sh} + I_c + I$$

Coupled system of equations:

$$(1) \quad -R_s C_0 \frac{\partial I}{\partial t} = I_s \left(e^{\frac{q(V+IR_s)}{nk_B T}} - 1 \right) + \left(\frac{R_s}{R_{sh}} + 1 \right) I + \frac{V}{R_{sh}} + C_0 \frac{\partial V}{\partial t} + \mathcal{A} \frac{\partial P_{nl}}{\partial t} - I_{ph}$$

$$(2) \quad \frac{\partial P_{nl}}{\partial t} = \frac{P_{nl,\infty}(U_c(t)) - P_{nl}(t)}{\tau} \quad \text{with} \quad P_{nl,\infty} = (U_c/V_{oc})P_{\infty}$$

Initial conditions: $I(t=0) = I_0 \quad P_{nl}(t=0) = P_0$.

$C(t)$ modeled as $P(t)$

$$P(t) = P_l(t) + P_{nl}(t)$$

$$P_l(t) = \epsilon_0 \chi_l E(t)$$

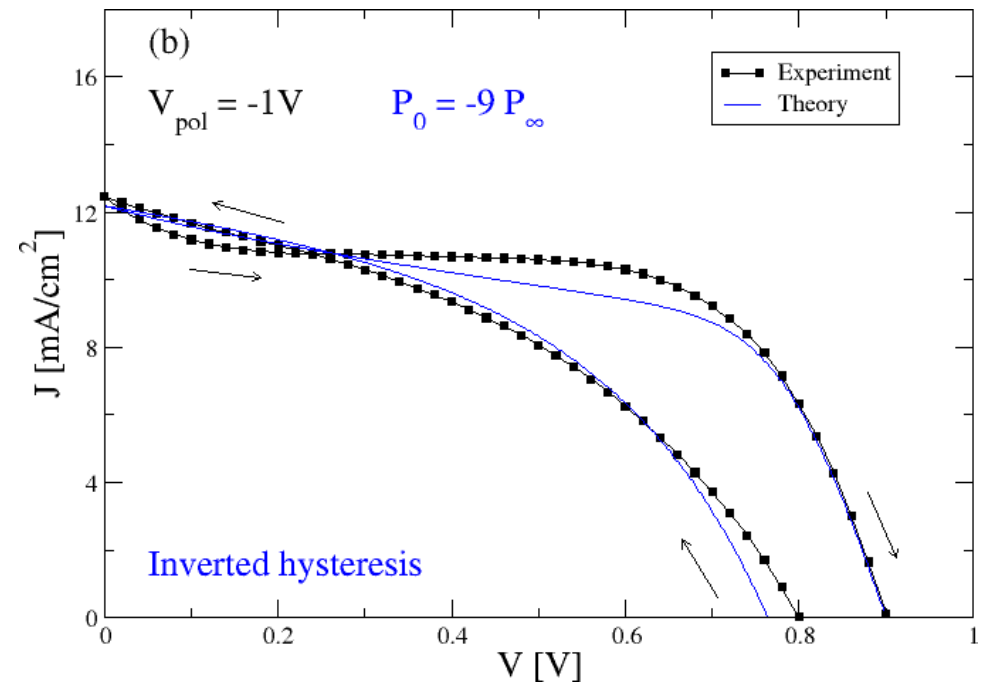
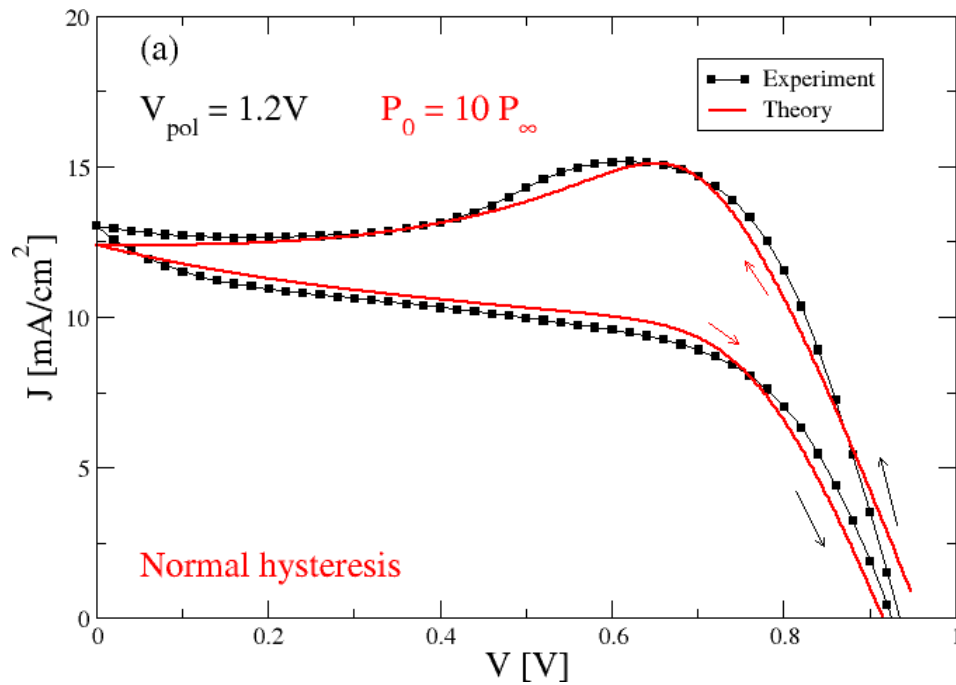
$$\epsilon = (1 + \chi_l) \epsilon_0$$

Capacitor current:

$$I_c = C_0 \frac{\partial U_c(t)}{\partial t} + \mathcal{A} \frac{\partial P_{nl}(t)}{\partial t}$$

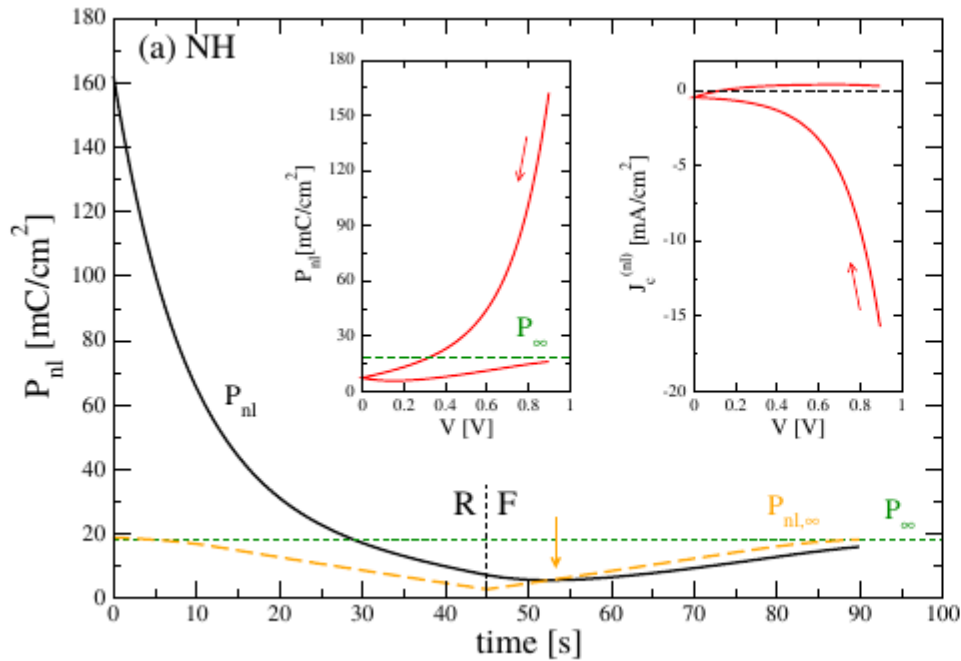
* G. A. Nemnes et al, "Dynamic electrical behavior of halide perovskite based solar cells", Solar Energy Materials and Solar Cells 159, 197 (2017)

Normal and inverted hysteresis

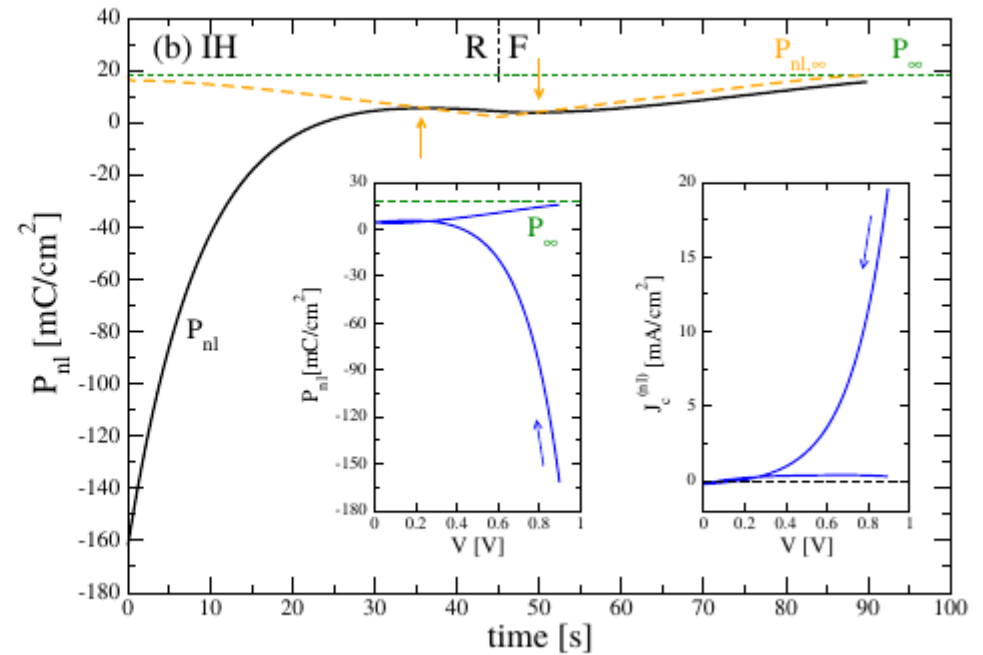


Dynamic electrical behavior of perovskite solar cells under bias pre-poling:
(a) *normal hysteresis* and (b) *inverted hysteresis*.

Normal and inverted hysteresis : $P_{nl}(t)$



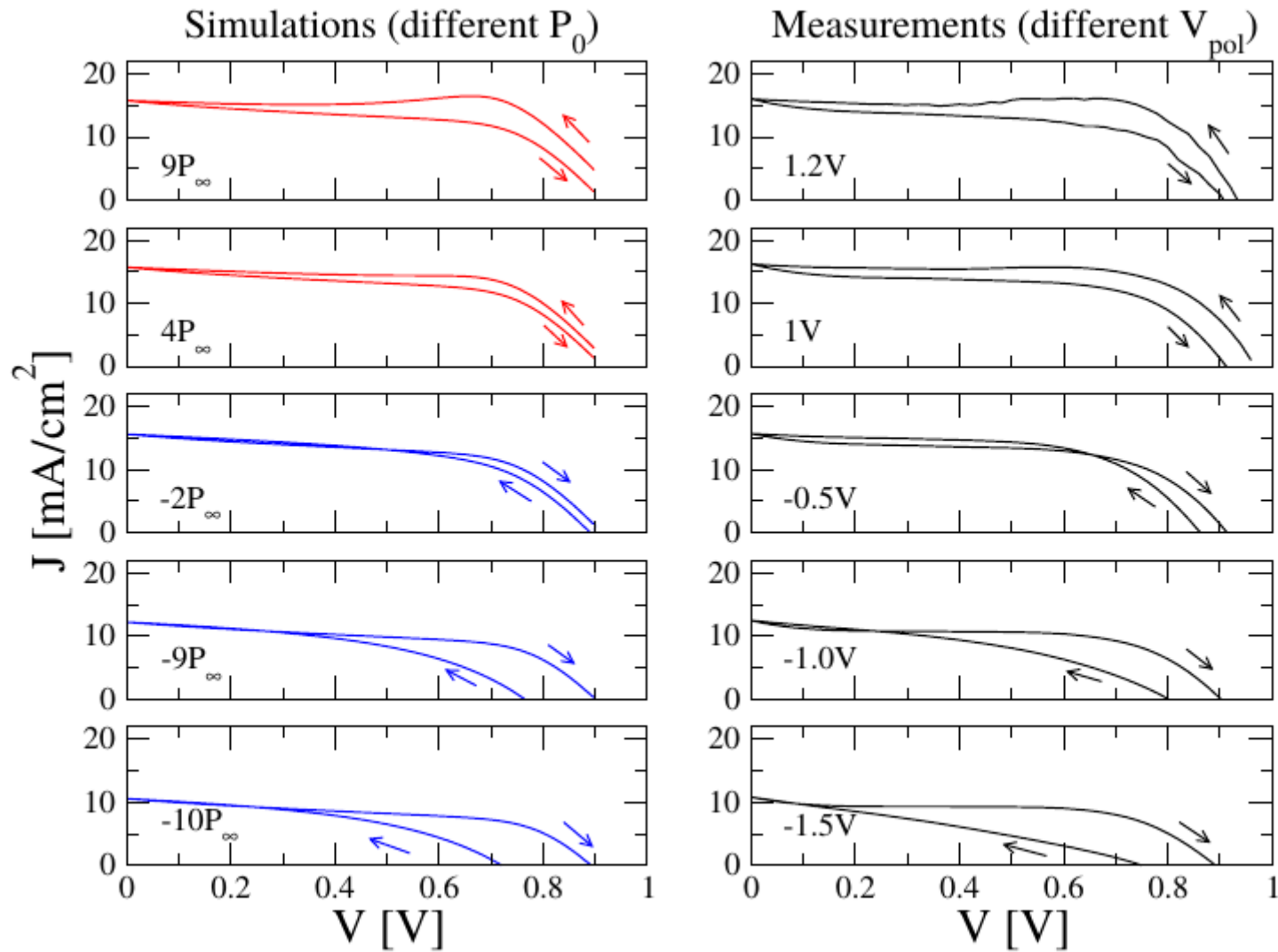
Normal hysteresis



Inverted hysteresis

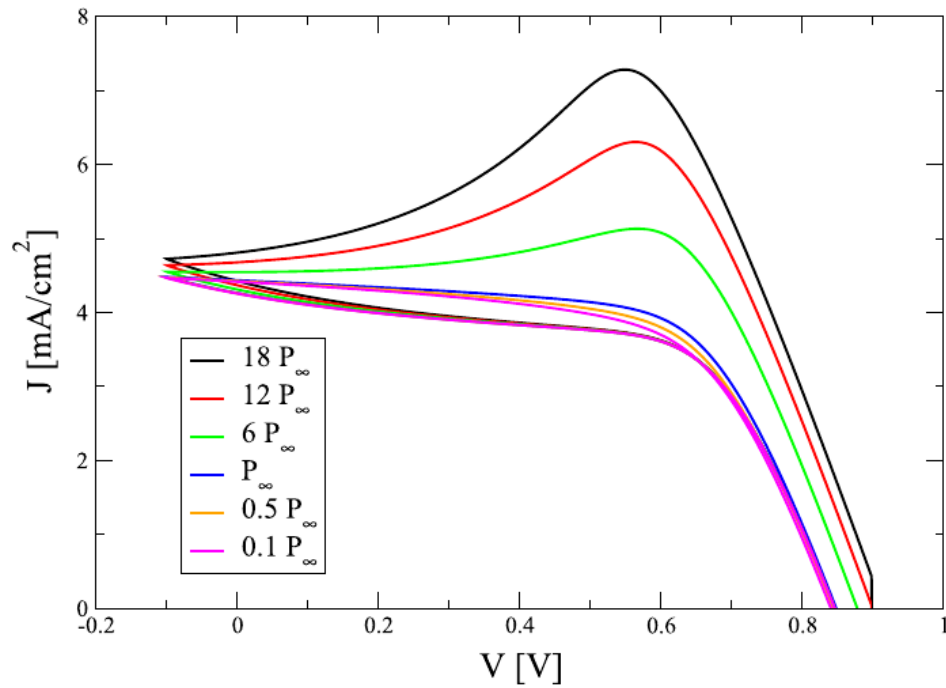
Time evolution of the non-linear polarization charge P_{nl} for NH (a) and IH (b).

Normal and inverted hysteresis

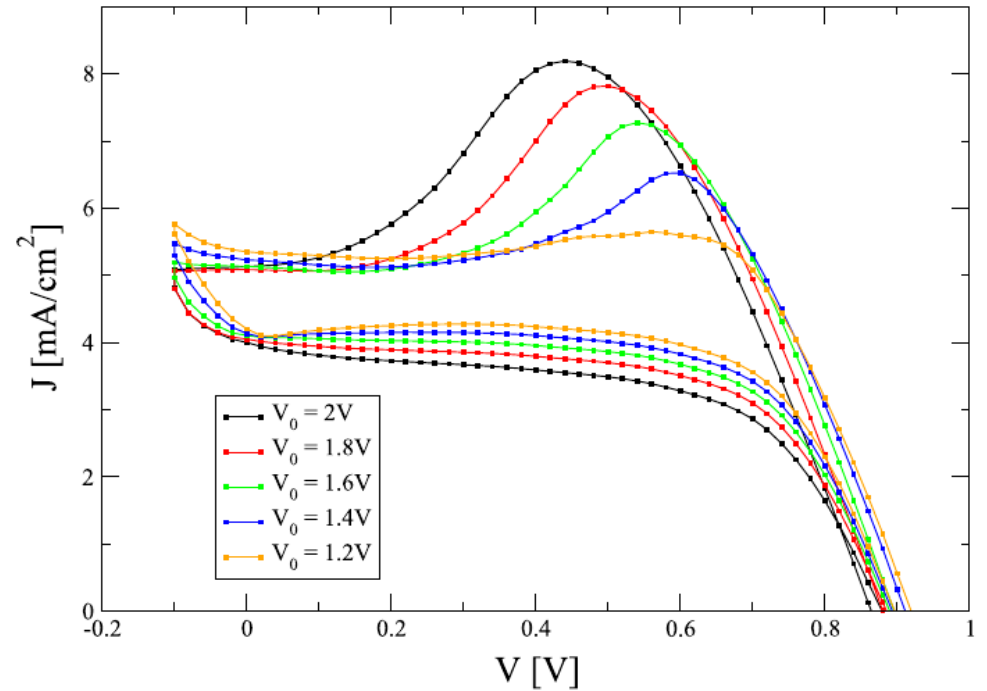


Simulation vs. experiment: effect of pre-poling bias.

Increasing the poling bias

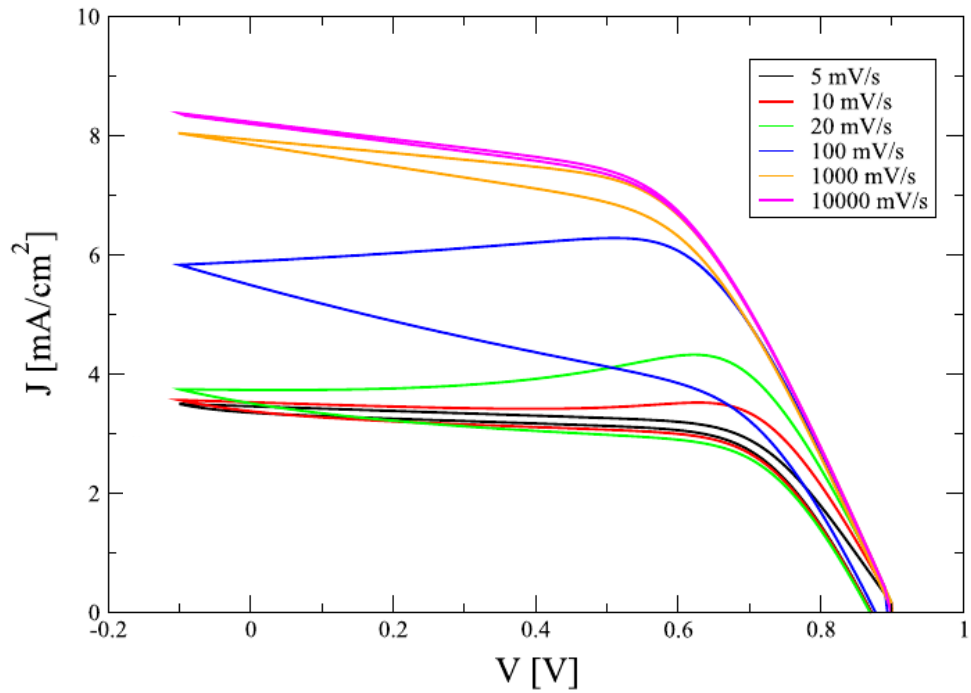


Theory (P0)

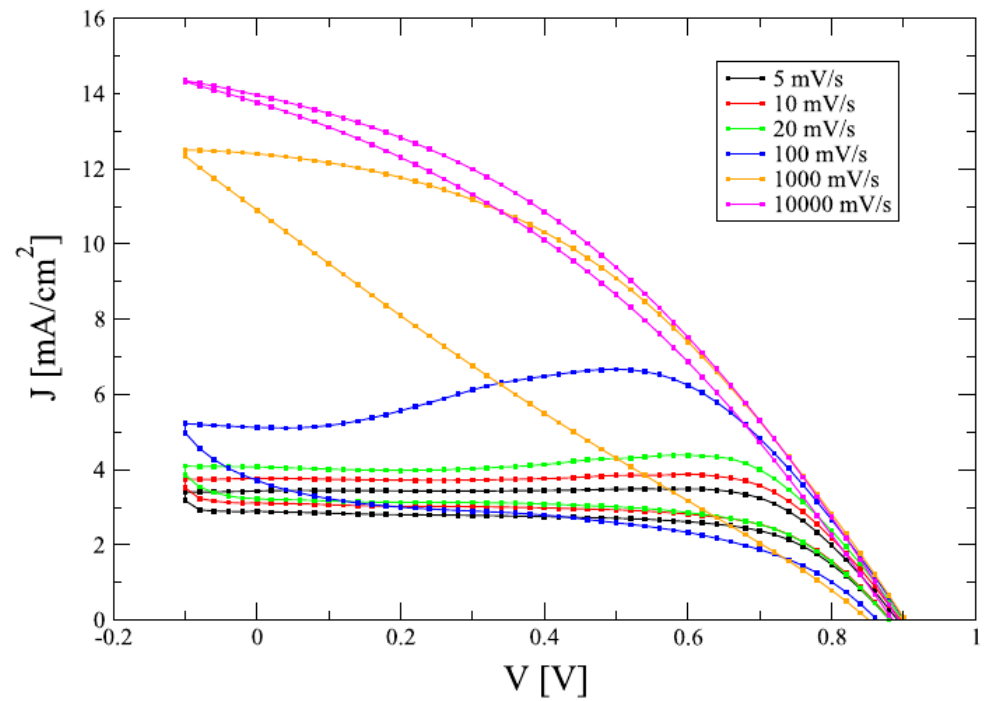


Experiment (V0)

Effect of the bias scan rate



Theory (dV/dt)



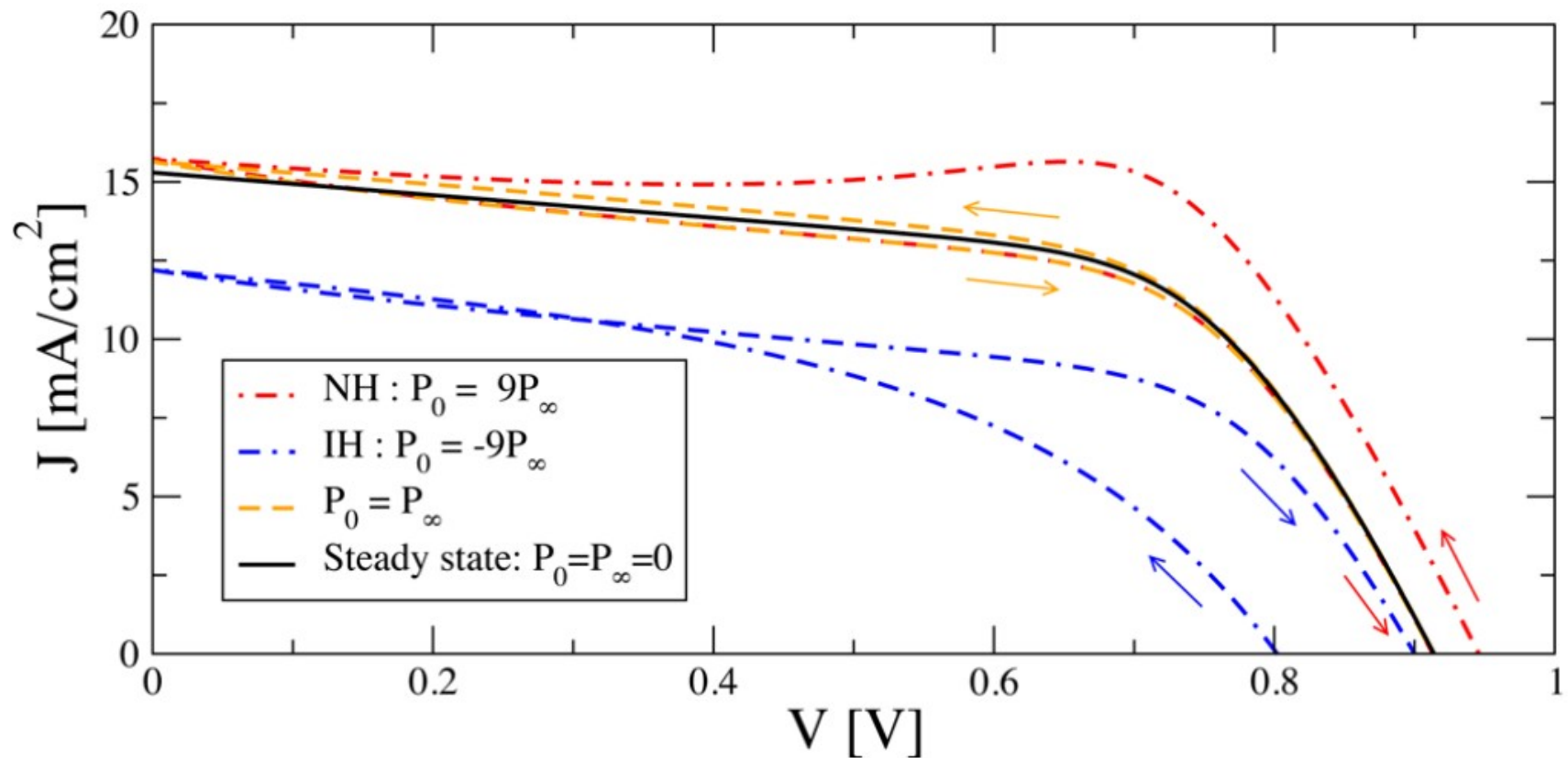
Experiment (dV/dt)

Measurement protocol

Three-step measurement protocol:

1. Stabilization at the open circuit bias $\rightarrow V_{oc}$
2. Bias pre-poling at V_{oc} for a time t_{pol}
3. Actual measurement:
A continuous reverse-forward sweep starting from V_{oc}

Measurement protocol



Comparing J-V characteristics at different bias pre-polarization conditions: over-polarization (NH), inverse polarization (IH), minimal polarization and steady state.

Conclusions

- A dynamic electrical model (DEM) was proposed in form of an equivalent circuit, where the capacitor current is modeled by the time variation of the non-linear polarization.
- A particularly simple *Ansatz* for the time dependence of P_{nl} was introduced, explaining the hysteretic behaviors: pre-poling effects (overshoot in the reverse current), the enhanced hysteresis at intermediate scan rates and the increase (NH) / decrease (IH) of the short-circuit current at high rates.
- Normal and inverted hysteresis may be obtained in the same sample, with different poling conditions. *The DEM unifies two apparently different forms of hysteresis.*
- The analysis of the hysteretic effects represents an important issue for a correct determination of the PCE → reliable measurement protocols are required!
- The DEM provides the framework and is a practical tool for the calibration of microscopic descriptions.

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- [2] G. A. Nemnes et al, “*Normal and inverted hysteresis in perovskite solar cells*”, J. Phys. Chem. C 121, 11207 (2017) ; ArXiv:1704.03300 (2017)